

SEMICONDUCTOR TECHNICAL DATA

2N3485A

2N3486A

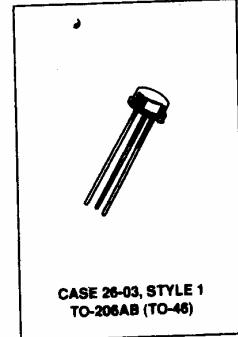
PNP Silicon Small-Signal Transistors

...designed for high-speed switching circuits and DC to VHF amplifier applications.

CRYSTALONCS
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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	60	Vdc
Collector-Base Voltage	V _{CBO}	60	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	Vdc
Collector Current	I _C	600	mAdc
Power Dissipation	P _T	0.4	Watts
@ T _A = 25°C		2.28	mW/°C
Derate above 25°C		2.0	Watts
@ T _C = 25°C		11.43	mW/°C
Derate above 25°C			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-65 to 200	°C



CASE 26-03, STYLE 1
TO-206AB (TO-46)

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ⁽¹⁾ (I _C = 10 mAdc, I _E = 0)	V _{(BR)CEO}	60	—	Vdc
Collector-Base Breakdown Voltage (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	—	Vdc
Base-Emitter Voltage (I _E = 10 μAdc, I _C = 0)	V _{(BR)EBO}	5.0	—	Vdc
Collector Cutoff Current (V _{CB} = 50 Vdc, I _E = 0) (V _{CB} = 50 Vdc, I _E = 0, T _A = 150°C)	I _{CBO}	—	10 10	nAdc μAdc
Emitter Cutoff Current (V _{EB} = 3.5 Vdc, I _C = 0)	I _{EBO}	—	50	nAdc

(continued)

(1) Pulsed. Pulse Width 250 to 350 μs. Duty Cycle 1.0 to 2.0%.

2N3485AJAN, 2N3486AJAN SERIES

ELECTRICAL CHARACTERISTICS — continued ($T_A = 25^\circ C$ unless otherwise noted)					
Characteristic	Symbol	Min	Max	Unit	
ON CHARACTERISTICS					
DC Current Gain ($I_C = 0.1 \text{ mA}_\text{dc}$, $V_{CE} = 10 \text{ V}_\text{dc}$)	2N3485A 2N3486A	h_{FE}	40 75	—	—
($I_C = 1.0 \text{ mA}_\text{dc}$, $V_{CE} = 10 \text{ V}_\text{dc}$)	2N3485A 2N3486A		40 100	—	—
($I_C = 10 \text{ mA}_\text{dc}$, $V_{CE} = 10 \text{ V}_\text{dc}$)	2N3485A 2N3486A		40 100	—	—
($I_C = 150 \text{ mA}_\text{dc}$, $V_{CE} = 10 \text{ V}_\text{dc}$) ⁽¹⁾	2N3485A 2N3486A		40 100	120 300	—
($I_C = 500 \text{ mA}_\text{dc}$, $V_{CE} = 10 \text{ V}_\text{dc}$) ⁽¹⁾	2N3485A 2N3486A		40 50	— —	—
($I_C = 1.0 \text{ mA}_\text{dc}$, $V_{CE} = 10 \text{ V}_\text{dc}$, $T_A = -65^\circ C$)	2N3485A 2N3486A		20 40	— —	—
Collector-Emitter Saturation Voltage ⁽¹⁾ ($I_C = 150 \text{ mA}_\text{dc}$, $I_B = 15 \text{ mA}_\text{dc}$) ($I_C = 500 \text{ mA}_\text{dc}$, $I_B = 50 \text{ mA}_\text{dc}$)	V _{CE(sat)}		— —	0.4 1.6	V _{dc}
Base-Emitter Saturation Voltage ⁽¹⁾ ($I_C = 150 \text{ mA}_\text{dc}$, $I_B = 15 \text{ mA}_\text{dc}$) ($I_C = 500 \text{ mA}_\text{dc}$, $I_B = 50 \text{ mA}_\text{dc}$)	V _{BE(sat)}		— —	1.3 2.6	V _{dc}
SMALL-SIGNAL CHARACTERISTICS					
Current Gain ($I_C = 1.0 \text{ mA}_\text{dc}$, $V_{CE} = 10 \text{ V}_\text{dc}$, $f = 1.0 \text{ kHz}$)	2N3485A 2N3486A	h_{fe}	40 100	— —	—
Small-Signal Current Transfer Ratio, Magnitude ($I_C = 50 \text{ mA}_\text{dc}$, $V_{CE} = 20 \text{ V}_\text{dc}$, $f = 100 \text{ MHz}$)		$ h_{fe} $	2.0	10	—
Output Capacitance ($V_{CB} = 10 \text{ V}_\text{dc}$, $f = 0.1$ to 1.0 MHz)	C _{obo}		—	8.0	pF
Input Capacitance ($V_{EB} = 2.0 \text{ V}_\text{dc}$, $f = 0.1$ to 1.0 MHz)	C _{iob}		—	30	pF
SWITCHING CHARACTERISTICS (See Figures 31 & 39)					
Turn-On Time	2N3485A 2N3486A	t _{on}	—	175	ns
Turn-Off Time		t _{off}	—	200	ns
Turn-On + Turn-Off Time (Non-Saturated Switching)		t _{on} + t _{off}	—	18	ns
ASSURANCE TESTING (Pre/Post Burn-In)					
Burn-in Conditions: $T_A = +25^\circ C$, $V_{CB} = 30 \text{ V}_\text{dc}$ $P_T = 400 \text{ mW}$					
Characteristics Tested	Symbol	Initial and End Point Limits			Unit
		Min	Max		
Collector Cutoff Current ($V_{CB} = 50 \text{ V}_\text{dc}$)	I _{CBO}	—	10	nA _{dc}	—
DC Current Gain ⁽¹⁾ ($I_C = 150 \text{ mA}_\text{dc}$, $V_{CE} = 10 \text{ V}_\text{dc}$)	2N3485A 2N3486A	h_{FE}	40 100	120 300	—
Delta from Pre-Burn-In Measured Values					
Delta Collector Cutoff Current	ΔI_{CBO}	—	± 100 or ± 5.0 whichever is greater	% of Initial Value nA _{dc}	—
Delta DC Current Gain ⁽¹⁾	Δh_{FE}	—	± 15	% of Initial Value	—

⁽¹⁾ Pulsed Pulse Width 250 to 350 μs . Duty Cycle 1.0 to 2.0%.